

Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	40				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.0016				
$R_{DS(on)}$ (Ω) at V_{GS} = 4.5 V	0.0019				
I _D (A)	120				
Configuration	Single				



N-Channel MOSFET

FEATURES

- TrenchFET[®] power MOSFET
- · Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified d
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ORDERING INFORMATION				
Package	TO-263			
Lead (Pb)-free and Halogen-free	SQM40010EL-GE3			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current ^a	T _C = 25 °C	- I _D	120		
	T _C = 125 °C		120		
Continuous Source Current (Diode Conduction) ^a	I _S	120	А		
Pulsed Drain Current ^b		I _{DM}		300	
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	80		
Single Pulse Avalanche Energy		E _{AS}	320	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	- P _D	375	W	
	T _C = 125 °C		125	vv	
Operating Junction and Storage Temperature Range		TJ, T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)		R _{thJC}	0.4	0/10	

Notes

a. Package limited.

b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

c. When mounted on 1" square PCB (FR4 material).

d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$		40	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		2.0	2.5		
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 40 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	2	mA	
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	120	-	-	Α	
		$V_{GS} = 10 V$	I _D = 30 A	-	0.00121	0.00160		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 V$	$I_D = 30 \text{ A}, \text{T}_\text{J} = 125 \ ^\circ\text{C}$	-	-	0.00250	Ω	
Drain-Source On-State Resistance	- 103(01)	$V_{GS} = 10 V$	$I_D = 30 \text{ A}, \text{T}_\text{J} = 175 \ ^\circ\text{C}$	-	-	0.00280		
			$V_{GS} = 4.5 \text{ V}$ $I_D = 20 \text{ A}$		0.00145		<u> </u>	
Forward Transconductance b	9 _{fs}	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 30 \text{ A}$		-	174	-	S	
Dynamic ^b					1			
Input Capacitance	C _{iss}			-	13 630	17 100		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{GS} = 0 \ V \qquad V_{DS} = 20 \ V, \ f = 1 \ MHz$		8660	10 900	pF	
Reverse Transfer Capacitance	C _{rss}			-	1460	1900		
Total Gate Charge ^c	Qg			-	150	230		
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 \text{ V}$	$V_{DS} = 20 \text{ V}, I_D = 100 \text{ A}$	-	30	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	12	-	1	
Gate Resistance	Rg	f = 1 MHz		0.8	1.62	2.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 0.2 \Omega$ $\text{I}_{D} \cong 100 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	14	25		
Rise Time ^c	t _r			-	20	30		
Turn-Off Delay Time ^c	t _{d(off)}			-	60	90	ns	
Fall Time ^c	t _f			-	14	25		
Source-Drain Diode Ratings and Char	acteristics b							
Pulsed Current ^a	I _{SM}			-	-	300	А	
Forward Voltage	V _{SD}	$I_{\rm F} = 70 \text{ A}, V_{\rm GS} = 0 \text{ V}$		-	0.85	1.5	V	
5	00	1						

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

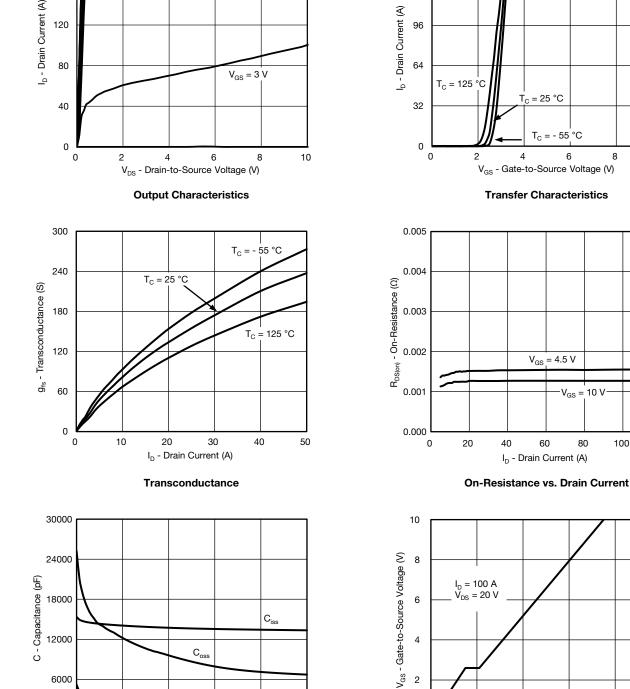
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

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 $V_{GS} = 10$ V thru 4 V

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C_{rss}

V_{DS} - Drain-to-Source Voltage (V)

Capacitance

Q_g - Total Gate Charge (nC)

Gate Charge

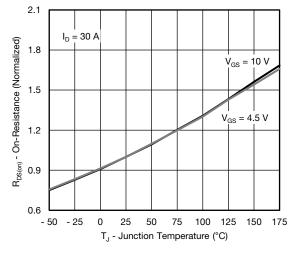
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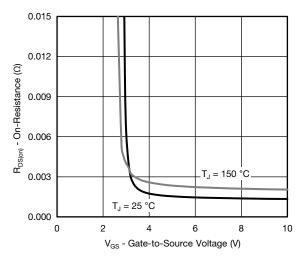


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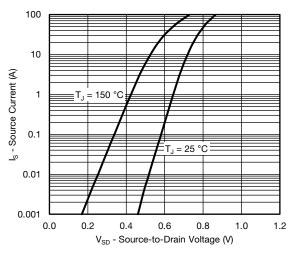
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



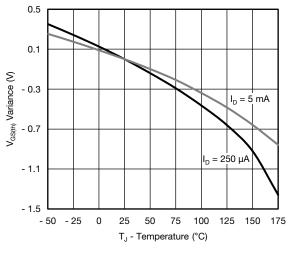




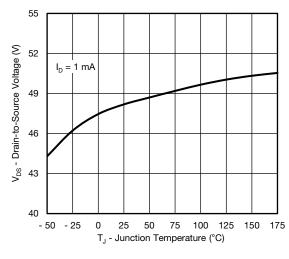
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







Drain Source Breakdown vs. Junction Temperature 4

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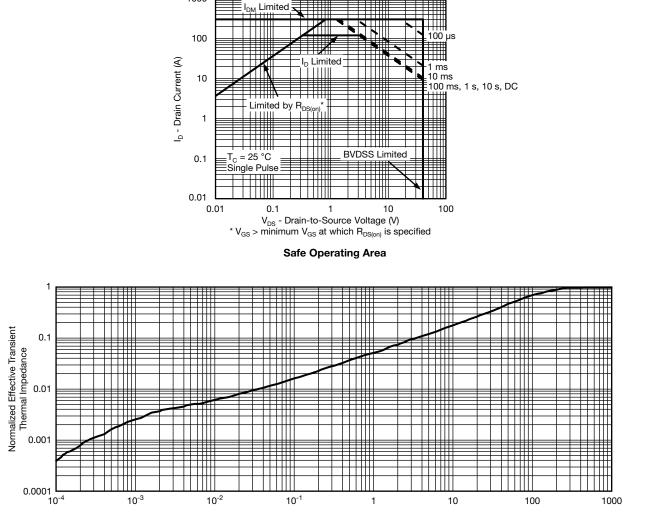
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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)

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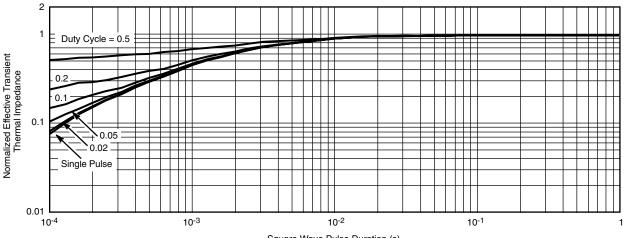
Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Square Wave Pulse Duration (s)

Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

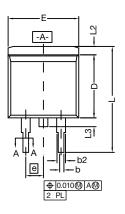
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

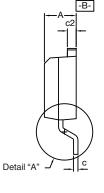
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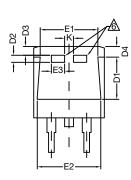


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TO-263 (D²PAK): 3-LEAD









DETAIL A (ROTATED 90°)



		INCHES		MILLIMETERS		
DIM.		MIN.	MAX.	MIN.	MAX.	
А		0.160	0.190	4.064	4.826	
	b	0.020	0.039	0.508	0.990	
	b1	0.020	0.035	0.508	0.889	
	b2	0.045	0.055	1.143	1.397	
c*	Thin lead	0.013	0.018	0.330	0.457	
С	Thick lead	0.023	0.028	0.584	0.711	
c1	Thin lead	0.013	0.017	0.330	0.431	
CI	Thick lead	0.023	0.027	0.584	0.685	
	c2	0.045	0.055	1.143	1.397	
	D	0.340	0.380	8.636	9.652	
	D1	0.220	0.240	5.588	6.096	
	D2	0.038	0.042	0.965	1.067	
D3		0.045	0.055	1.143	1.397	
	D4	0.044	0.052	1.118	1.321	
E		0.380	0.410	9.652	10.414	
E1		0.245	-	6.223	-	
E2		0.355	0.375	9.017	9.525	
E3		0.072	0.078	1.829	1.981	
	е	0.100 BSC		2.54 BSC		
	К	0.045	0.055	1.143	1.397	
L		0.575	0.625	14.605	15.875	
L1		0.090	0.110	2.286	2.794	
L2		0.040	0.055	1.016	1.397	
L3		0.050	0.070	1.270	1.778	
	L4	0.010 BSC		0.254 BSC		
М		-	0.002	-	0.050	
ECN: T13-0707-Rev. K, 30-Sep-13 DWG: 5843						

Notes

- 1. Plane B includes maximum features of heat sink tab and plastic. 2. No more than 25 $\,\%\,$ of L1 can fall above seating plane by
- max. 8 mils.3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB.
 - Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

This feature is for thick lead.

Revison: 30-Sep-13



RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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